

isc Silicon NPN RF Transistor

2SC4264

DESCRIPTION

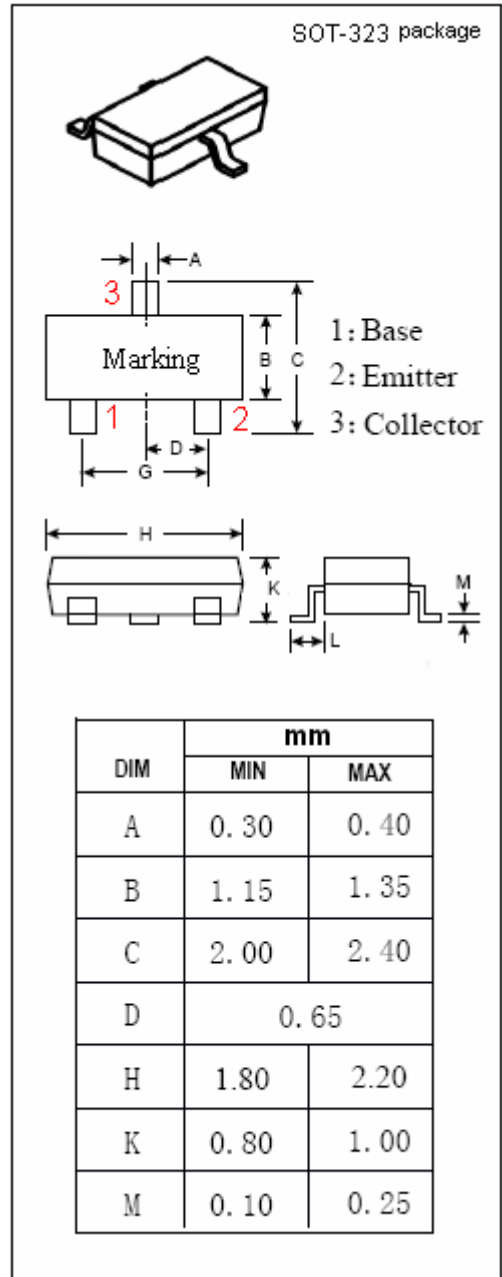
- Low Noise
- High Gain

APPLICATIONS

- Designed for use in UHF ~VHF RF amplifier, local oscillator, mixer.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	20	V
V_{CEO}	Collector-Emitter Voltage	11	V
V_{EBO}	Emitter-Base Voltage	3.0	V
I_C	Collector Current-Continuous	50	mA
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	0.1	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



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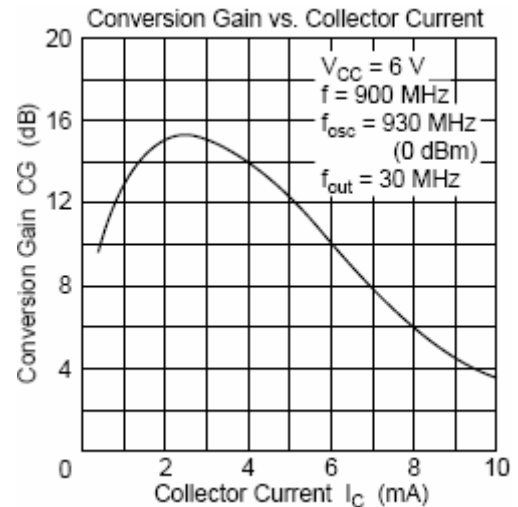
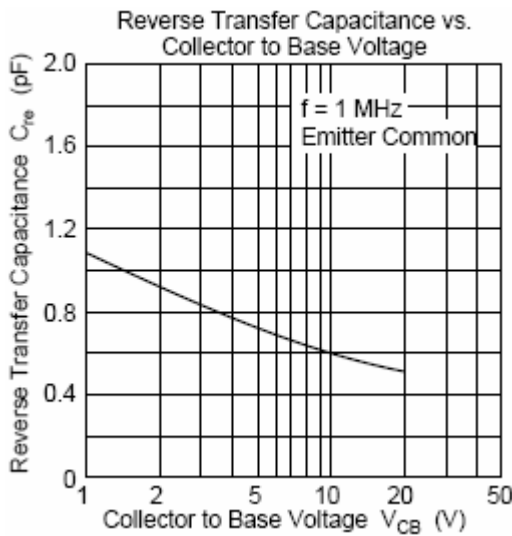
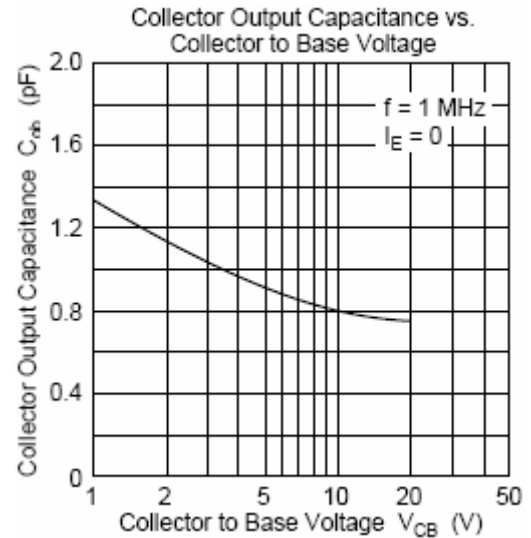
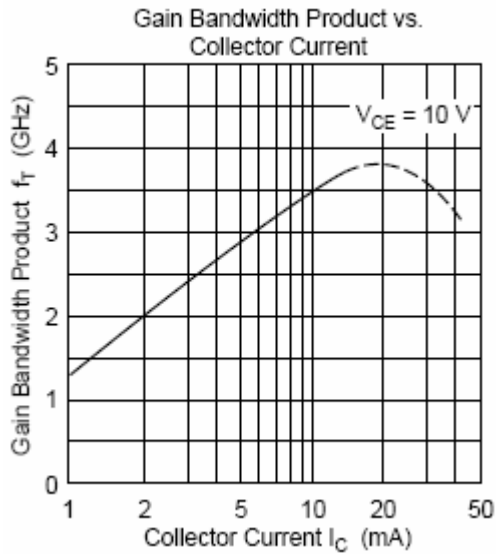
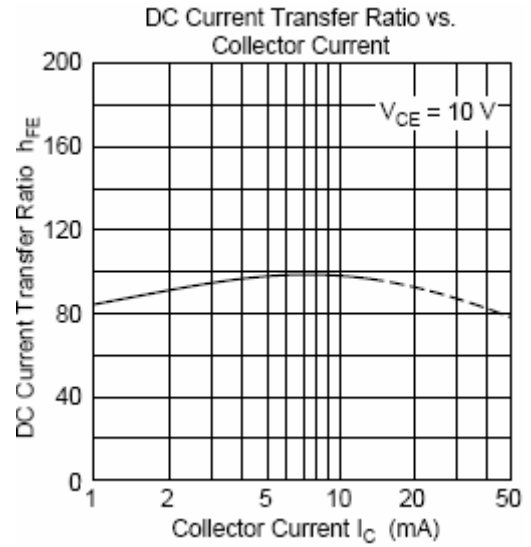
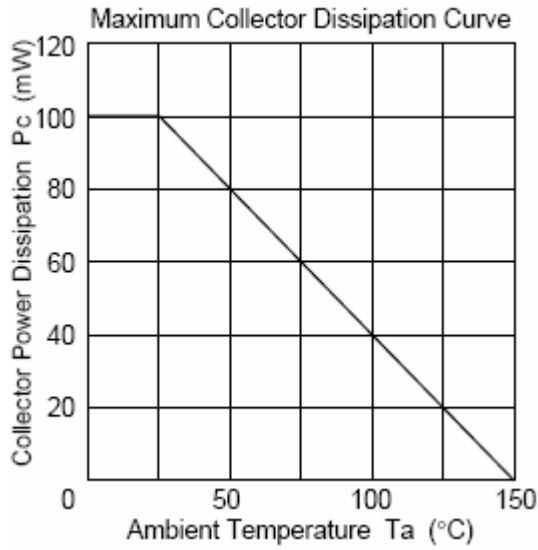
ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=10\mu\text{A}; I_E=0$	20			V
I_{CBO}	Collector Cutoff Current	$V_{CB}=15\text{V}; I_E=0$			0.5	μA
I_{CEO}	Collector Cutoff Current	$V_{CE}=11\text{V}; R_{BE}=\infty$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=3\text{V}; I_C=0$			1.0	μA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{mA}; I_B=5\text{mA}$			0.7	V
h_{FE}	DC Current Gain	$I_C=5\text{mA}; V_{CE}=10\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C=10\text{mA}; V_{CE}=10\text{V}$	1.4			GHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1.0\text{MHz}$			1.5	pF

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